

Abstract of the Disclosure

5 The present invention provides a nitride semiconductor light emitting device with an active layer of the multiple quantum well structure, in which the device has an improved luminous intensity and a good electrostatic withstanding voltage, thereby allowing the expanded application to various products. The active layer 7 is formed of a multiple quantum well structure containing $\text{In}_a\text{Ga}_{1-a}\text{N}$ ($0 \leq a < 1$). The p-cladding layer 8 is formed on said active layer containing the p-type impurity. The p-cladding layer 8 is made of a multi-film layer including a first nitride semiconductor film containing Al and a second nitride semiconductor film having a composition different from that of said first nitride semiconductor film. Alternatively, the p-cladding layer 8 is made of single-layered layer made of $\text{Al}_b\text{Ga}_{1-b}\text{N}$ ($0 \leq b \leq 1$). A low-doped layer 9 is grown on the p-cladding layer 8 having a p-type impurity concentration lower than that of the p-cladding layer 8. A p-contact layer is grown on the low-doped layer 9 having a p-type impurity concentration higher than those of the p-cladding layer 8 and the low-doped layer 9.